



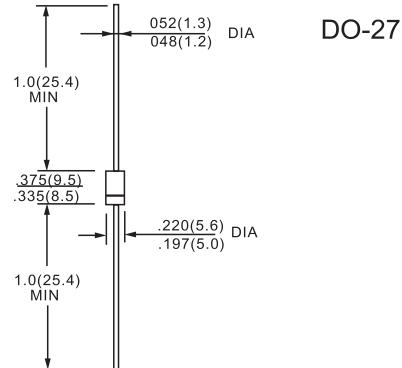
**VISHAY MAS
GENERAL SEMICONDUCTOR**

90SQ030 THRU 90SQ045

30V-45V 9.0A

FEATURES

- 175°C T_J operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

VOLTAGE RATINGS

PARAMETER	SYMBOL	90SQ030	90SQ035	90SQ040	90SQ045	UNITS
Maximum DC reverse voltage	V_R	30	35	40	45	V
Maximum working peak reverse voltage	V_{RWM}					

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average forward current See fig. 5	$I_{F(AV)}$	50 % duty cycle at $T_C = 69^\circ\text{C}$, rectangular waveform		9	A	
Maximum peak one cycle non-repetitive surge current See fig. 7	I_{FSM}	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated V_{RRM} applied	2150		
		10 ms sine or 6 ms rect. pulse		340		
Non-repetitive avalanche energy	E_{AS}	$T_J = 25^\circ\text{C}$, $I_{AS} = 1.8 \text{ A}$, $L = 7.4 \text{ mH}$		12	mJ	
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 μs Frequency limited by, T_J maximum $V_A = 1.5 \times V_R$ typical		1.8	A	

ELECTRICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum forward voltage drop See fig. 1	$V_{FM}^{(1)}$	9 A	$T_J = 25^\circ\text{C}$	0.48	V	
		18 A		0.57		
		9 A	$T_J = 125^\circ\text{C}$	0.42		
		18 A		0.52		
Maximum reverse leakage current See fig. 2	$I_{RM}^{(1)}$	$T_J = 25^\circ\text{C}$	$V_R = \text{Rated } V_R$	1.75	mA	
		$T_J = 125^\circ\text{C}$		70		
Maximum junction capacitance	C_T	$V_R = 5 \text{ V}_{DC}$, (test signal range 100 kHz to 1 MHz) 25°C		900	pF	
Typical series inductance	L_S	Measured lead to lead 5 mm from body		10.0	nH	
Maximum voltage rate of change	dV/dt	Rated V_R		10 000	V/ μs	

THERMAL - MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	T_J , T_{Stg}			- 55 to 150	°C
Maximum thermal resistance, junction to lead	$R_{th, JL}$	DC operation; see fig. 4 1/8" lead length		8.0	°C/W
Typical thermal resistance, junction to air	$R_{th, JA}$			44	
Approximate weight				1.4	g
				0.049	oz.
Marking device		Case style DO-204AR (JEDEC)		90SQ030	
				90SQ035	
				90SQ040	
				90SQ045	



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RATINGS AND CHARACTERISTIC CURVES 90SQ030 THRU 90SQ045

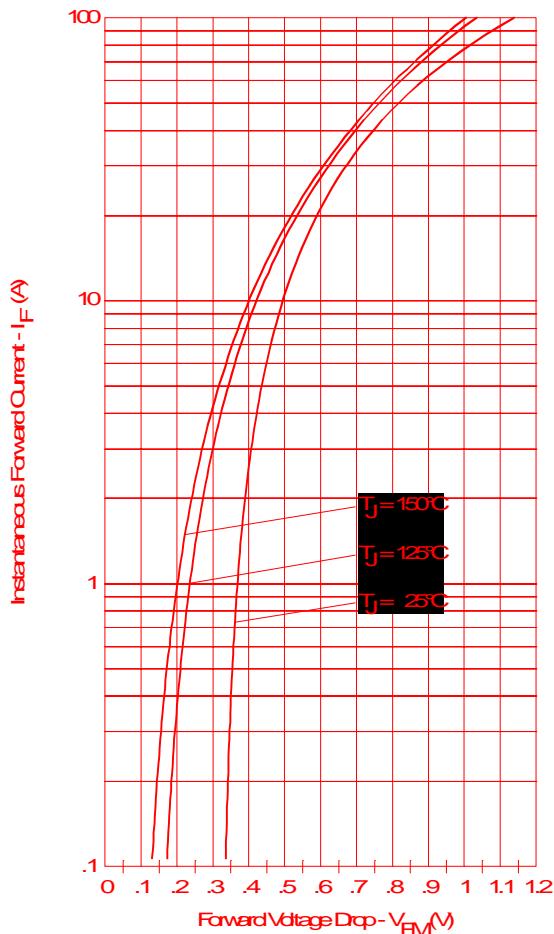


Fig. 1 - Maximum Forward Voltage Drop Characteristics

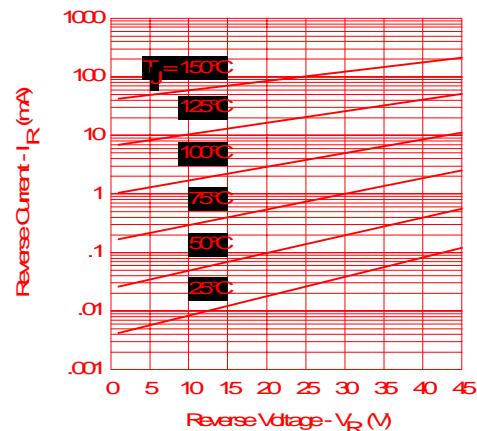


Fig. 2 - Typical Values of Reverse Current
Vs. Reverse Voltage

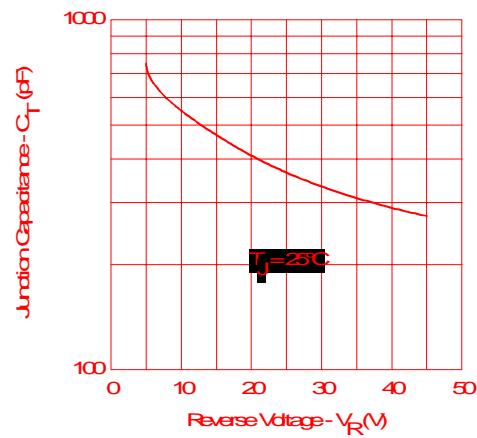


Fig. 3 - Typical Junction Capacitance
Vs. Reverse Voltage

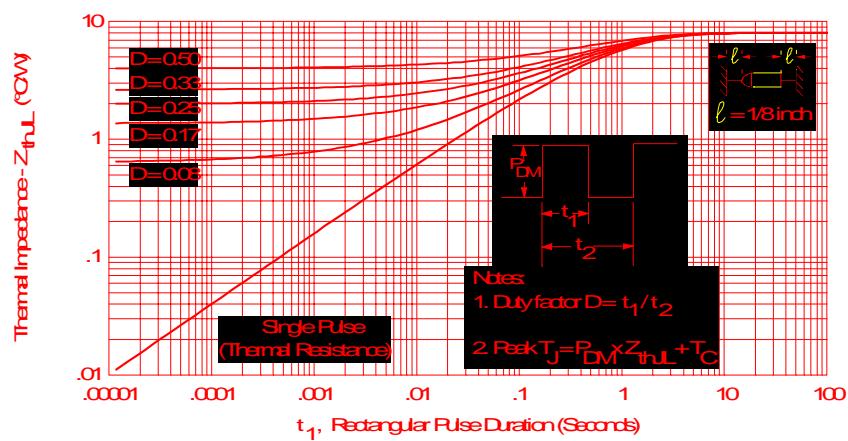


Fig. 4 - Maximum Thermal Impedance Z Characteristics



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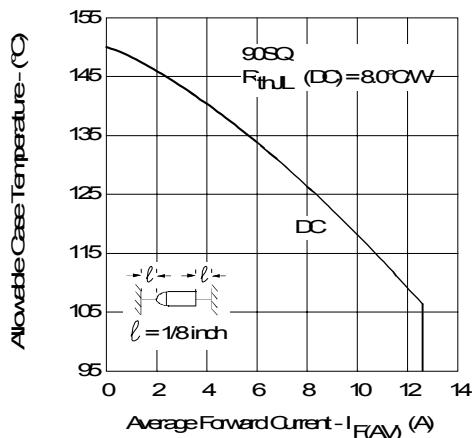


Fig. 5-Maximum Allowable Case Temperature Vs. Average Forward Current

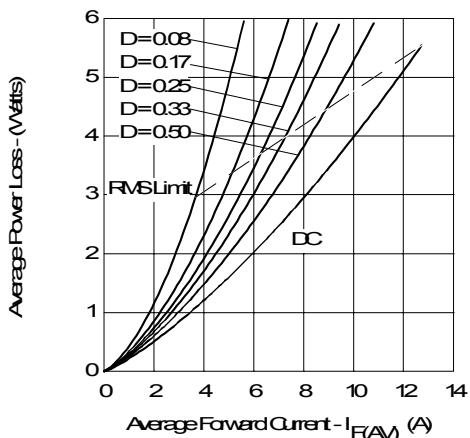


Fig. 6-Forward Power Loss Characteristics

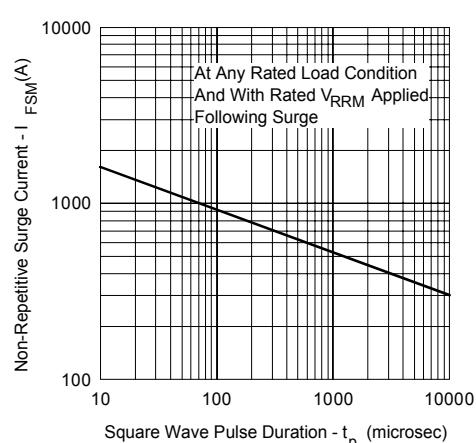


Fig. 7-Maximum Non-Repetitive Surge Current

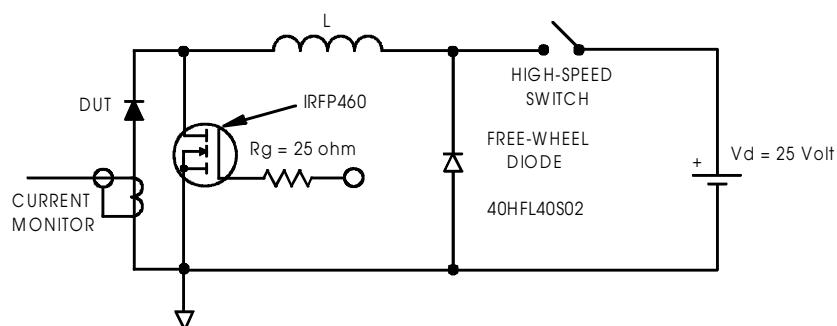


Fig. 8-Unclamped Inductive Test Circuit